Plastic Infrared Emitting Diode

OP265FAA Series

Obsolete (OP265FAC)

Electronics

Features:

- T-1 (3 mm) package style
- Narrow irradiance pattern
- Dome lens
- Higher power output than GaAs at equivalent drive currents



Description:

Each device in the OP265FAA series is a high intensity gallium arsenide infrared emitting diode (GaAlAs) that is molded in an IR transmissive clear epoxy package with a dome lens. Devices feature a narrow source irradiance pattern and a variety of electrical characteristics. The small T-1 package style makes these devices ideal for space-limited applications.

These devices are mechanically and spectrally matched to other OPTEK products as follows:

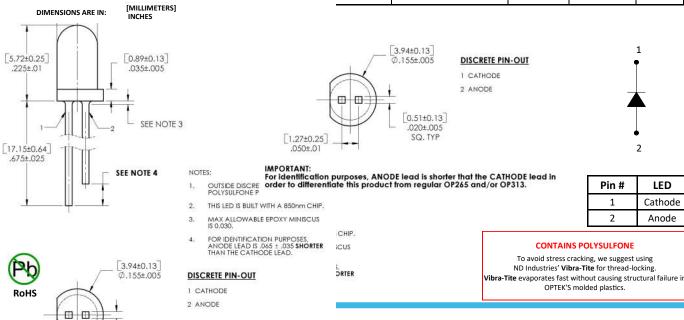
OP265 devices conform to the OP505 and OP535 series devices.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

- Space-limited applications
- Applications requiring coupling efficiency
- Battery-operated or voltage-limited applications

Ordering Information									
Part LED Peak Number Wavelength		Output Power (mW/cm²) Min / Max	I _F (mA) Typ / Max	Total Beam Angle	Lead Length				
OP265FAA		5.5 / NA		18°	0.50"				
OP265FAB	850 nm	7.5 / 12.5	20 / 50						
OP265FAC		11.5 / 16.5							



TT Electronics | OPTEK Technology 2900 E. Plano Pkwy, Plano, TX 75074 | Ph: +1 972 323 2200 www.ttelectronics.com | sensors@ttelectronics.com

LED

Cathode

Anode

1.27±0.25

.050±.01

0.51±0.13 .020±.005

SQ. TYP

Plastic Infrared Emitting Diode

OP265FAA Series Obsolete (OP265FAC)



Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage and Operating Temperature Range	-40° C to +100° C
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾
Power Dissipation	100 mW ⁽²⁾

Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 second maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.
- 2. Derate linearly at 1.33 mW/° C above 25° C.
- 3. E_{E(APT)} is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens and 0.590" (14.99 mm) from the measurement surface. E_{E(APT)} is not necessarily uniform within the measured area.

Electrical Characteristics (T_A = 25° C unless otherwise noted)

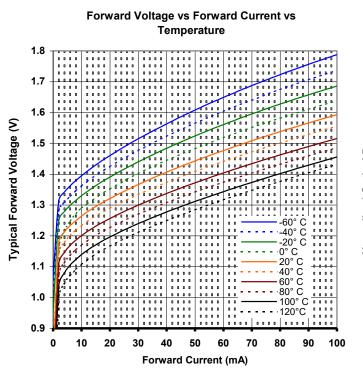
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS			
Input Diode									
E _{E(APT)}	Apertured Radiant Incidence OP265FAA OP265FAB	5.50 7.50	-	- 12.5	mW/cm²	I_F = 20 mA Aperture = 0.081" diameter Distance = 0.590" from seating surface to aperture surface			
V_{F}	Forward Voltage	-	-	1.80	V	I _F = 20 mA			
I _R	Reverse Current	-	10	-	μΑ	V _R = 10 V			
λ_{P}	Wavelength at Peak Emission	-	850	-	nm	I _F = 10 mA			
$\Delta\lambda_P/\Delta T$	Spectral Shift with Temperature	-	±0.18	-	nm/° C	I _F = Constant			
θ_{HP}	Emission Angle at Half Power Points	-	18	-	Degree	I _F = 20 mA			
t _r	Output Rise Time		10	-	ns	I _{F(PK)} = 100 mA, PW = 10 μs, D.C. = 10.0 %			
t _f	Output Fall Time	-	10	-	ns	I _{F(PK)} = 100 mA, PW = 10 μs, D.C. = 10.0 %			

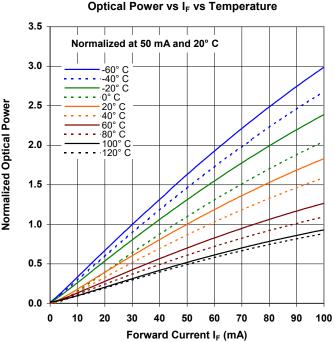
Plastic Infrared Emitting Diode

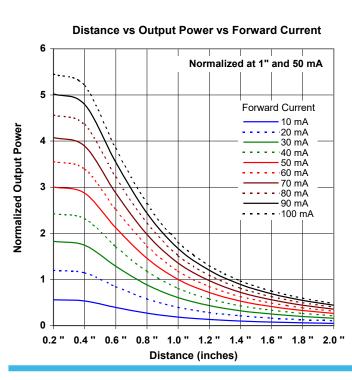
OP265FAA Series Obsolete (OP265FAC)

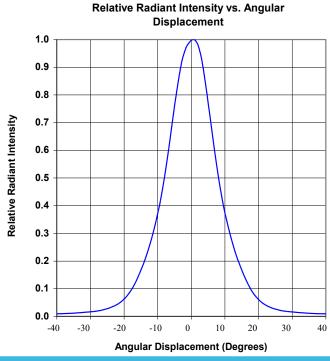


Performance OP265F (AA, AB)









General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.